2SC458, 2SC2308

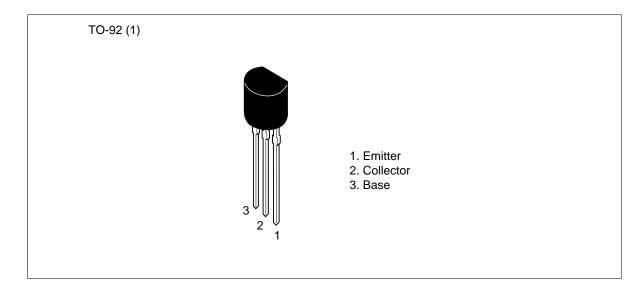
Silicon NPN Epitaxial

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Application

- Low frequency amplifier
- Complementary pair with 2SA1029 and 2SA1030

Outline





2SC458, 2SC2308

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SC458	2SC2308	Unit
Collector to base voltage	V_{CBO}	30	55	V
Collector to emitter voltage	V_{CEO}	30	50	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I _c	100	100	mA
Emitter current	I _E	-100	-100	mA
Collector power dissipation	P _c	200	200	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

		2SC4	58		2SC2308				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	55	_	_	V	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	_	_	50	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	_	_	0.5	μΑ	$V_{CB} = 18 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	100	_	500	100	_	320		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.2	_	_	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	0.67	0.75	_	0.67	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Gain bandwidth product	\mathbf{f}_{T}	_	230	_	_	230	_	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	1.8	3.5	_	1.8	3.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	4	10	_	4	10	dB	$V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$ $f = 1 \text{ kHz}, R_{g} = 500 \Omega$
Small signal input impedance	h _{ie}	_	16.5	_	_	16.5	_	kΩ	$V_{CE} = 5V, I_{C} = 0.1 \text{mA},$ f = 270 Hz
Small signal voltage feedback ratio	h _{re}	_	70	_	_	70	_	× 10 ⁻⁶	
Small signal current trancefer ratio	h _{fe}	_	130	_	_	130	_		-
Small signal output admittance	h _{oe}	_	11.0	_	_	11.0	_	μS	_

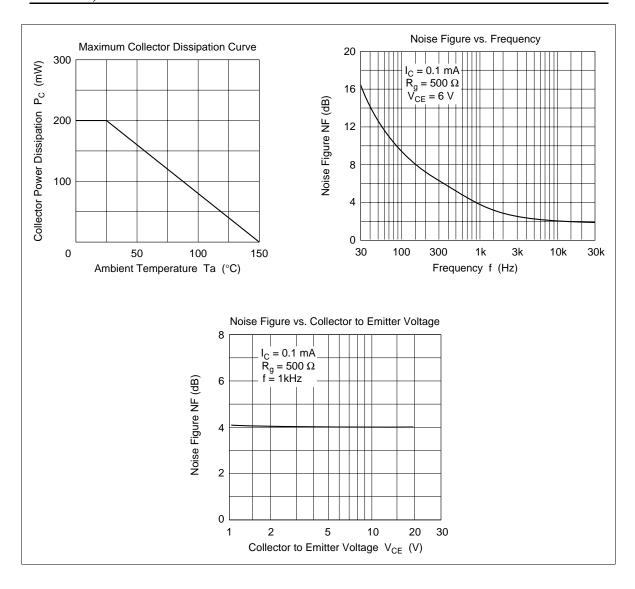
Note: 1. The 2SC458 and 2SC2308 are grouped by $h_{\rm FE}$ as follows.

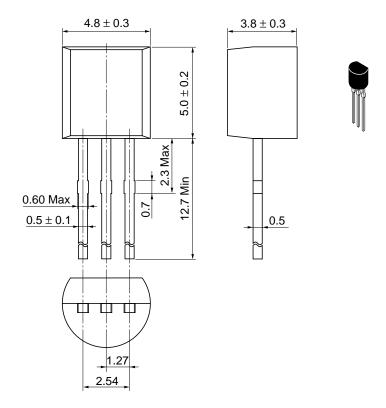
	В	С	D
2SC458	100 to 200	160 to 320	250 to 500
2SC2308	100 to 200	160 to 320	_

See characteristic curves of 2SC458 (LG) and 2SC2310 except for the followings.

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2SC458, 2SC2308





Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive. San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park

Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Lower Cookham Road

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

Telex: 40815 HITEC HX

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